

2SC2315 2SC2316

Silicon NPN Triple Diffused Mesa

☆ Super Beta Transistor

Application Example:
General Purpose

● Outline Drawing 1MT-25(TO220)

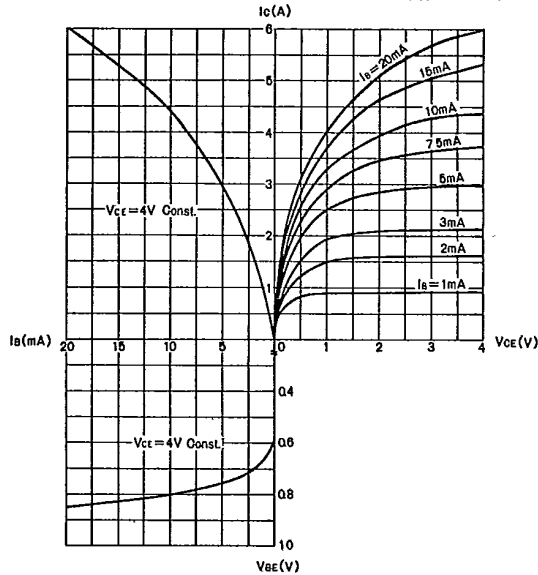
Absolute Maximum Ratings

Symbol	2SC2315	2SC2316	Unit
V_{CBO}	80	100	V
V_{CEO}	60	80	V
V_{EBO}	6		V
I_C	6		A
I_B	3		A
P_C	50 ($T_{FL}=25^\circ C$)		W
T_J	150		$^\circ C$
T_{stg}	-55~+150		$^\circ C$

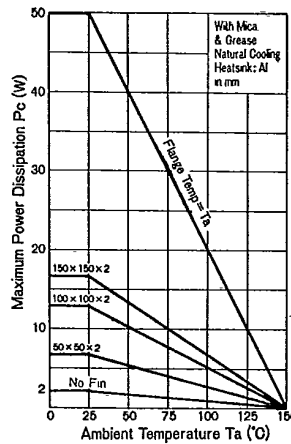
Electrical Characteristics

Symbol	Conditions	2SC2315	2SC2316	Unit
I_{CBO}	$V_{CB} =$	100max	100max	μA
I_{EBO}	$V_{EB} = 6V$	80	100	V
$V_{(BR)CEO}$	$I_C = 25mA$	60min	80min	V
h_{FE}	$V_{CE} = 4V, I_C = 0.5A$	500min		
$V_{CE(sat)}$	$I_C = 3A, I_B = 0.06A$	1.0max		V
f_T	$V_{CE} = 12V, I_E = -0.5A$	30typ		MHz

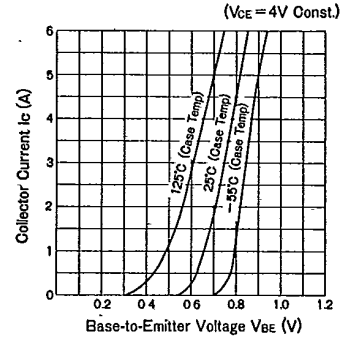
Common Emitter Characteristics (Typical Value)



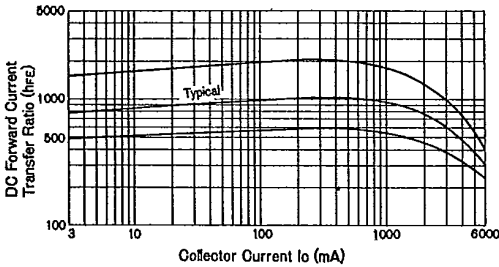
Power Derating



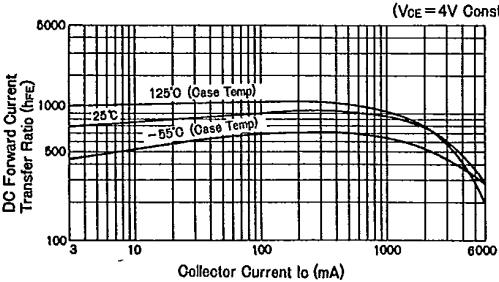
Temperature Characteristics



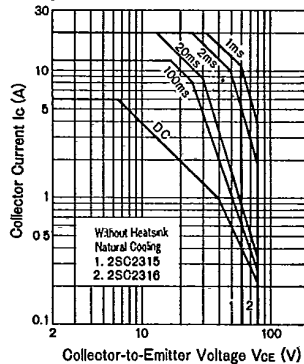
DC Current Gain Characteristics



DC Current Gain Temperature Characteristics



Maximum Areas For Safe Operation (ASO) (Single Pulse)



Collector-to-Emitter Saturation Characteristics

